## Supplementary Material

Structure No.	Туре	Electrode system	Working	The area of		Microchip size					
			electrode	Working	Distance*						
			size*	electrode							
#8	PVD	Two-electrode	R=1.5 mm	$7.065 \text{ mm}^2$	D=750 μm	12 mm×45 mm					
#9	PVD	Two-electrode	R=1.5 mm	$7.065 \text{ mm}^2$	D=200 μm	12 mm×45 mm					
#10	PVD	Two-electrode	R=900 μm	2.543 mm <sup>2</sup>	D=350 μm	13 mm×13 mm					
#11	PVD	Two-electrode	R=900 µm	2.543 mm <sup>2</sup>	D=500 µm	13 mm×13 mm					
#12	PVD	Two-electrode	R=900 µm	2.543 mm <sup>2</sup>	D=750 μm	13 mm×13 mm					

Table S1	. Relevant	parameters	of five	PVD	microchip	os.
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\* R means the radius of circular electrode. D means the distance between working electrode and counter electrode.



Fig. S1. ECL intensity from 0.1  $\mu$ M Ru(bpy)<sub>3</sub><sup>2+</sup> and 30 mM TPrA in PBS solution (0.01 M, pH 7.0), achieved in SPE and PVD microchips with a 1500- $\mu$ m radius of WE. Labeled value represents the distance between the counter electrode and working electrode for each microchip. The dots in each line represent ECL intensity during the measurement under different TP in the range of 1.5 V to 2.8 V.



Fig. S2. ECL intensity from 0.1  $\mu$ M Ru(bpy)<sub>3</sub><sup>2+</sup> and 30 mM TPrA in PBS solution (0.01 M, pH 7.0), achieved in PVD microchips with identical WE area (a 900- $\mu$ m radius of WE) and different distance between WE and CE. The dots in each line represent ECL intensity during the measurement under different TP in the range of 1.5 V to 3.0 V.



Fig. S3. Calibration plots for the TPrA determination using PVD chip (#4) with a 900-µm radius of WE. The buffer is 0.01 M PBS solution, and the concentration of  $Ru(bpy)_3^{2+}$  was 10 µM. Five replicate measurements were performed for all devices. Data were reported as average ± standard deviation. The X and Y axes were in a logarithmic scale to obtain a more condensed graphical representation.